

PNP BSV15 – BSV16 – BSV17

MEDIUM POWER TRANSISTORS

They are silicon transistors mounted in TO-39 metal package.
They are intended for general industrial applications.
High current and low voltage.
Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CBO}	Collector-Base Voltage $I_E = 0$	BSV15	-40	V
		BSV16	-60	
		BSV17	-90	
V_{CEO}	Collector-Emitter Voltage $I_B = 0$	BSV15	-40	V
		BSV16	-60	
		BSV17	-90	
V_{EBO}	Emitter-Base Voltage $I_C = 0$		-5	V
I_C	Collector Current		-1	A
I_{CM}	Peak Collector Current		-2	A
I_{BM}	Peak Base Current		-0.2	A
P_{tot}	Total Power Dissipation	@ $T_{case} = < 25^\circ$	0.8	W
		@ $T_{amb} = < 25^\circ$	5	
		@ $T_{mb} = < 50^\circ$	5	
T_J	Junction Temperature		200	$^\circ\text{C}$
T_{Stg}	Storage Temperature Range		-65 to +150	$^\circ\text{C}$
T_{amb}	Operating Ambient Temperature		-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-c}	Thermal Resistance, Junction-case	35	K/ W
$R_{thJ-amb}$	Thermal Resistance, Junction-ambient in free air	220	K/ W
R_{thJ-mb}	Thermal Resistance, Junction to mounting base	30	K/ W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit	
I_{CBO}	Collector – Cutoff Current	$I_E = 0, V_{CB} = -40\text{ V}$		-	-	-100	nA	
		$I_E = 0, V_{CB} = -60\text{ V}$						
		$I_E = 0, V_{CB} = -80\text{ V}$						
		$I_E = 0, V_{T_{amb}} = 150^{\circ}\text{C}$	$V_{CB} = -40\text{ V}$	BSV15	-	-	-50	μA
			$V_{CB} = -60\text{ V}$	BSV16				
			$V_{CB} = -80\text{ V}$	BSV17				
I_{EBO}	Emitter – Cutoff Current	$I_C = 0, V_{CE} = -4\text{V}$		-	-	-50	nA	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -500\text{ mA}, I_B = -25\text{ mA}$		-	-	-1	V	
V_{BE}	Base-Emitter Voltage (*)	$I_C = -100\text{ mA}, V_{CE} = -1\text{V}$		-	-	-1		
		$I_C = -500\text{ mA}, V_{CE} = -1\text{V}$		-	-	-1	V	
h_{FE}	DC Current Gain (*)	$I_C = -100\text{ }\mu\text{A}$ $V_{CE} = -1\text{ V}$	Gr.10	BSV15	20	75	-	-
				BSV16				
				BSV17				
			Gr.16	BSV15	30	120	-	
				BSV16				
		$I_C = -100\text{ mA}$ $V_{CE} = -1\text{ V}$	Gr.10	BSV15	63	100	160	
				BSV16				
				BSV17				
			Gr.16	BSV15	100	160	250	
				BSV16				
$I_C = -500\text{ mA}$ $V_{CE} = -1\text{ V}$	Gr.10	BSV15	25	55	-			
		BSV16						
		BSV17						
	Gr.16	BSV15	35	85	-			
		BSV16						

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ELECTRICAL CHARACTERISTICS

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Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit
f _T	Transition Frequency	I _C = -50 mA, V _{CE} = -10 V f=100 MHz		50	-	-	MH _Z
C _C	Collector Capacitance	I _E = i _e = 0, V _{CB} = -10V f = 1 MH _Z	BSV15	-	20	30	pF
			BSV16				
			BSV17	-	15	25	
C _E	Emitter Capacitance	I _E = i _e = 0, V _{CB} = -10V f = 1 MH _Z		-	180	-	pF

SWITCHING TIME

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
t_{off}	Turn-off times	$I_C = -100 \text{ mA}$ $I_{Bon} = -5 \text{ mA}$ $I_{Boff} = 5 \text{ mA}$	-	-	650	ns
t_{on}	Turn-on times		-	-	500	ns

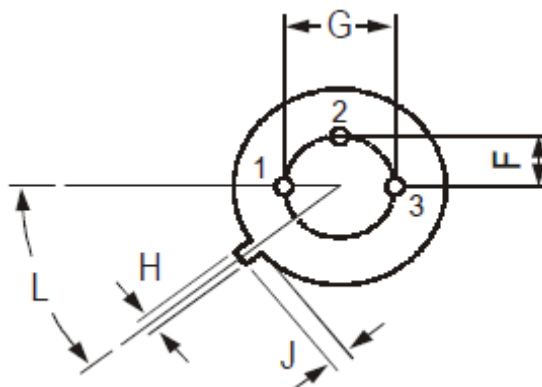
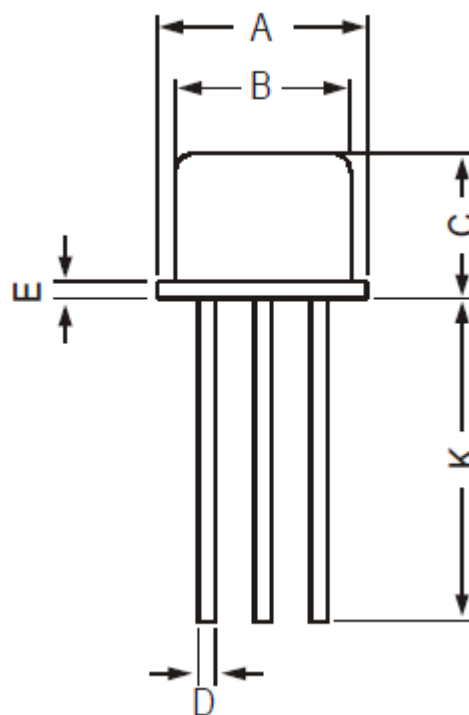
(*) Pulsed : pulse duration = 300μs, duty cycle = 1%

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MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)		
	min	max
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	-
L	42°	48°

Pin 1 :	Emitter
Pin 2 :	Base
Pin 3 :	Collector
Case :	Collector



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